

TSM05N03

30V N-Channel MOSFET



SOT-223

69 3

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
30	60 @ V _{GS} =10V	5	
	90 @ V _{GS} =4.5V	3.8	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

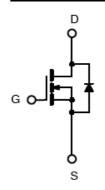
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM05N03CW RPG	SOT-223	2.5Kpcs / 13" Reel

Note: "G" denotes Halogen Free Product.

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	5	А	
Pulsed Drain Current		I _{DM}	±20	А	
Continuous Source Current (Diode Condu	rent (Diode Conduction) ^{a,b}		1.7	А	
Maximum Power Dissipation	Ta = 25°C	P _D	3	W	
	Ta = 75°C		1.1		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	15	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	45	°C/W

Notes

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on a 1 in² pad of 2oz Cu, $t \le 5$ sec.



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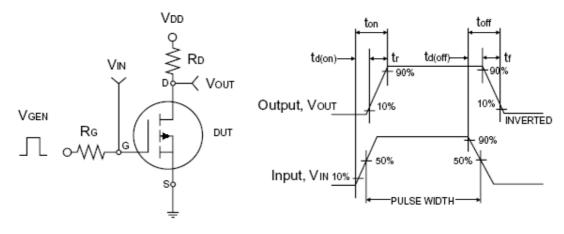


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1		3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}	1		1.0	μΑ
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 10V$	I _{D(ON)}	5			Α
Proin Course On State Besistance	$V_{GS} = 10V, I_D = 5A$		1	46	60	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 3.8A$	$R_{DS(ON)}$		70	90	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 5A$	g _{fs}		5		S
Diode Forward Voltage	$I_S = 2.5A, V_{GS} = 0V$	V_{SD}			1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 10V, I_{D} = 5A,$ $V_{GS} = 5V$	Q_g		4.2	7	
Gate-Source Charge		Q_{gs}		1.9		nC
Gate-Drain Charge	v _{GS} = 3 v	Q_{gd}		1.35		
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C_{iss}		555		
Output Capacitance		C _{oss}		120		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		60		
Switching ^{b.c}						
Turn-On Delay Time	V 40V D 450	t _{d(on)}	1	4.2	5.5	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 15\Omega,$ $I_D = 1A, V_{GEN} = 10V,$	t _r	1	19	25	~ C
Turn-Off Delay Time		t _{d(off)}	1	13	17	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		9	12	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

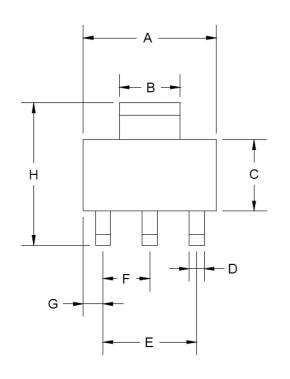


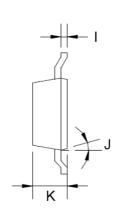
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SOT-223 Mechanical Drawing





SOT-223 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX	
Α	6.350	6.850	0.250	0.270	
В	2.900	3.100	0.114	0.122	
С	3.450	3.750	0.136	0.148	
D	0.595	0.635	0.023	0.025	
Е	4.550	4.650	0.179	0.183	
F	2.250	2.350	0.088	0.093	
G	0.835	1.035	0.032	0.041	
Н	6.700	7.300	0.263	0.287	
I	0.250	0.355	0.010	0.014	
J	10°	16°	10°	16°	
K	1.550	1.800	0.061	0.071	



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